





IFNU410, IFNU411, IFNU412 Dual Matched N-Channel JFET

Support

Features

- InterFET N0016H Geometry
- Low Leakage: 10 pA Typical
- Low Input Capacitance: 3.5 pF Typical
- High Input Impedance
- Replacement for U410, U411, U412
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

Applications

- Low Noise Differential Amplifier
- Differential Amplifier
- · Wide-Band Amplifier

Description

The -40V InterFET IFNU410, IFNU411, and IFNU412 JFET's are targeted for low noise differential amplifier designs. Gate leakages are less than 10pA at room temperatures. The TO-71 package is hermetically sealed and suitable for military applications. Custom specifications, matching, and packaging options are available.



| | Parameters | IFNU410 Min | IFNU411 Min | IFNU412 Min | Unit |
|----------------------|------------------------------------|-------------|-------------|-------------|------|
| BV _{GSS} | Gate to Source Breakdown Voltage | -40 | -40 | -40 | V |
| IDSS | Drain to Source Saturation Current | 0.5 | 0.5 | 0.5 | mA |
| V _{GS(off)} | Gate to Source Cutoff Voltage | -0.5 | -0.5 | -0.5 | V |
| GFS | Forward Transconductance | 1 | 1 | 1 | |
| | Forward Transconductance | 0.6 | 0.6 | 0.6 | 1115 |

Ordering Information Custom Part and Binning Options Available

| Part Number | Description | Case | Packaging |
|---------------------------|--|-------|--------------------|
| IFNU410; IFNU411; IFNU412 | Through-Hole | TO-71 | Bulk |
| SMPU410; SMPU411; SMPU412 | Surface Mount | SOIC8 | Bulk |
| | 7" Tape and Reel: Max 500 Pieces | | Minimum 500 Pieces |
| SMPU410; SMPU411; SMPU412 | 13" Tape and Reel: Max 2,500 Pieces | SOIC8 | Tape and Reel |
| IFNU410COT; IFNU411COT; | | | |
| IFNU412COT * | Chip Orientated Tray (COT Waffle Pack) | СОТ | 70/Waffle Pack |
| IFNU410CFT; IFNU411CFT; | | | |
| IFNU412CFT * | Chip Face-up Tray (CFT Waffle Pack) | CFT | 70/Waffle Pack |

* Bare die packaged options are designed for matched specifications but not 100% tested



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.





SOIC8 Top View











Support

Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

| | Parameters | Value | Unit |
|------------------|--|------------|-------|
| VRGS | Reverse Gate Source and Gate Drain Voltage | -40 | V |
| I _{FG} | Continuous Forward Gate Current | 50 | mA |
| PD | Continuous Device Power Dissipation | 375 | mW |
| Р | Power Derating | 3 | mW/°C |
| ΤJ | Operating Junction Temperature | -55 to 125 | °C |
| T _{STG} | Storage Temperature | -65 to 150 | °C |

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

| | | | IFNU410, IFNU411, IFNU412 | | | |
|----------------------|---------------------------------------|---|---------------------------|-----|------|------|
| | Parameters | Conditions | Min | Тур | Max | Unit |
| V _{(BR)GSS} | Gate to Source Breakdown Voltage | $I_G = -1\mu A, V_{DS} = 0V$ | -40 | | | v |
| I _{GSS} | Gate to Source Reverse Current | V _{GS} = -30V, V _{DS} = 0V | | | -0.2 | nA |
| lg | Gate Operating Current | V _{DS} = 10V, I _D = 200μA | | | -200 | pА |
| Vgs(off) | Gate to Source Cutoff Voltage | V _{DS} = 20V, I _D = 1nA | -0.5 | | -3.5 | V |
| V _{GS} | Gate Source Voltage | V _{DS} = 20V, I _D = 200µA | -0.2 | | -3 | v |
| IDSS | Drain to Source Saturation Current | $V_{DS} = 20V, V_{GS} = 0V$ (Pulsed) | 0.5 | | 5 | mA |

Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

| | | | | IFNU410, IFNU411, IFNU412 | | | |
|-----------------------|---------------------|--|---------------------|---------------------------|-----|-----|--------|
| Р | arameters | Conditions | | Min | Тур | Max | Unit |
| Gra | Forward | $V_{DS} = 20V, V_{GS} = 0V, f = 0V$ | = 1kHz | 1 | | 4 | ms |
| UFS | Transconductance | V_{DS} = 20V, I_{D} = 200 μ A, f | [:] = 1kHz | 0.6 | | 1.2 | 1115 |
| Gos | Output Conductance | $V_{DS} = 20V, V_{GS} = 0V, f =$ | = 1kHz | | 20 | | |
| Gus | Output conductance | V _{DS} = 20V, I _D = 200μA, f | = 1kHz | | | 5 | μ |
| C _{iss} | Input Capacitance | V_{DS} = 20V, V_{GS} = 0V, f = | 1MHz | | | 4.5 | pF |
| Crss | Reverse Capacitance | $V_{DS} = 20V, V_{GS} = 0V, f = 1MHz$ | | | | 1.2 | pF |
| e, | Equivalent Circuit | V _{DS} = 20V. I _D = 200µA. f | = 100Hz | | 20 | 70 | nV/√Hz |
| | Input Noise Voltage | 55 · , 5 · · · · · · · | | | - | - | , |
| | Differential Gate | | IFNU410 | | | 10 | |
| $ V_{GS1} - V_{GS2} $ | | $V_{DS} = 20V, I_D = -200 \mu A$ | IFNU411 | | | 20 | mV |
| | Source voltage | | IFNU412 | | | 40 | |
| | Differential Gate | $V_{} = 20V_{} = 200 \mu \Lambda$ | IFNU410 | | | 1 | |
| VGS1 - VGS2 | Source Voltage with | $v_{\rm DS} = 20v$, $i_{\rm D} = 200\mu A$ | IFNU411 | | | 2.5 | mV/°C |
| Δ1 | Temperature | $I_A = 25^{\circ}C, I_B = 85^{\circ}C$ | IFNU412 | | | 4 | |
| | Common Modo | Made $V = 10/(to 20)/$ | IFNU410 | | 80 | | |
| CMRR | | | IFNU411 | | 80 | | dB |
| | Rejection Ratio | id = 200μA | IFNU412 | | 70 | | |



Technical Order Now

Support

IFNU410-1-2

TO-71 Mechanical and Layout Data

Package Outline Data



Suggested Bent Lead Through-Hole Layout



- 1. All linear dimensions are in millimeters.
- 2. Eight leaded device. Not all leads are shown in drawing views.
- 3. Some package configurations will not populate pin 8 and/or pin 4.
- 4. Package weight approximately 0.35 grams
- 5. Bulk product is shipped in standard ESD shipping material
- 6. Refer to JEDEC standards for additional information.

- All linear dimensions are in millimeters. 1.
- Pads 8 and/or pad 4 can be eliminated for devices 2. with less pins.
- 3. The suggested land pattern dimensions have been provided as an eight pin bent lead reference only. A more robust pattern may be desired for wave soldering or reduced pin count.





SOIC8 Mechanical and Layout Data

Package Outline Data







Order

Now

- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.21 grams
- 3. Molded plastic case UL 94V-0 rated
- For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
- 5. Bulk product is shipped in standard ESD shipping material
- 6. Refer to JEDEC standards for additional information.

Suggested Pad Layout



- 1. All linear dimensions are in millimeters.
- 2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.

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